

<b>Ma</b>	Mounting torque (M3)	1.13/10
<b>Weight</b>	Typical	6

(T<sub>J</sub>=25°C, unless otherwise s

Symbol	Test Conditions	Characteristic Values		
		min.	typ.	max.
BV <sub>CES</sub>	I <sub>C</sub> =1mA; V <sub>GE</sub> =0V	1200		
V <sub>GE(th)</sub>	I <sub>C</sub> =750uA; V <sub>CE</sub> =V <sub>GE</sub>	5.0	5.8	6.5
I <sub>CES</sub>	V <sub>CE</sub> =V <sub>CES</sub> ; T <sub>J</sub> =25°C			250
	V <sub>GE</sub> =0V; T <sub>J</sub> =125°C			4
I <sub>GES</sub>	V <sub>CE</sub> =0V; V <sub>GE</sub> =±20V			±200
V <sub>CE(sat)</sub>	I <sub>C</sub> =I <sub>C90</sub> ; V <sub>GE</sub> =15V		2.7	2.9



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**Reverse Diode (FRED)**(T<sub>J</sub>=25°C, unless otherwise specified)

Symbol	Test Conditions	Characteristic Values		
		min.	typ.	max.
V <sub>F</sub>	I <sub>F</sub> =40A; T <sub>VJ</sub> =150°C T <sub>VJ</sub> =25°C		2.9 3.3	
I <sub>RM</sub>	V <sub>R</sub> =100V; I <sub>F</sub> =40A; -di <sub>F</sub> /dt=100A/us L ≤ 0.05uH; T <sub>VJ</sub> =100°C		12	
t <sub>rr</sub>	I <sub>F</sub> =1A; -di/dt=50A/us; V <sub>R</sub> =30V; T <sub>J</sub> =25°C		40	
R <sub>thJC</sub>	Diode		1.1	1.2



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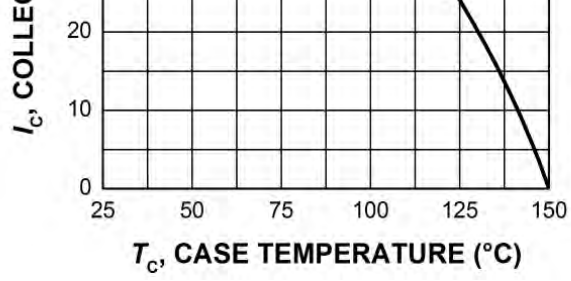


Figure 1. Maximum collector current as a function of case temperature ( $V_{GE} \geq 15V, T_j \leq 150^\circ C$ )

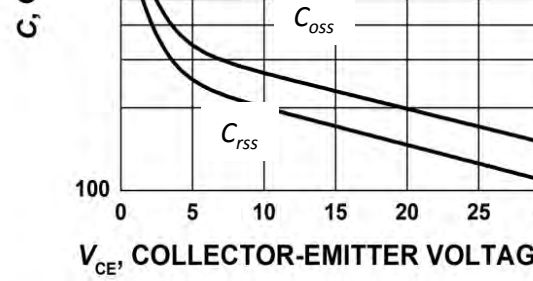


Figure 2. Typical capacitance as a function of collector-emitter voltage ( $V_{GE}=0V, f = 1$ )



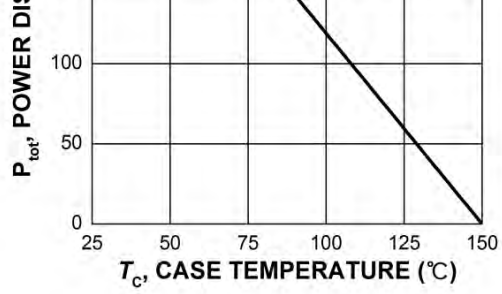


Figure 5. Maximum power dissipation as a function of case temperature ( $T_j \leq 150^\circ\text{C}$ )

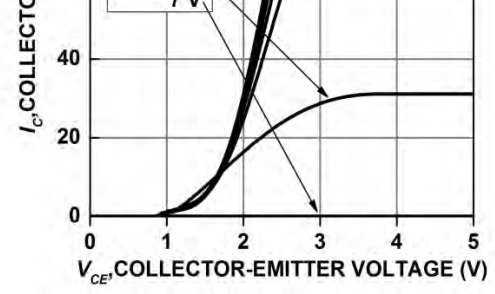


Figure 6. Typical output characteristic ( $T_j = 25^\circ\text{C}$ )



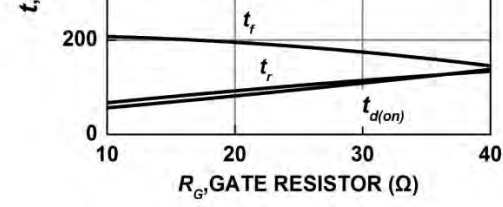


Figure 9. Typical switching times as a function of gate resistor (inductive load,  $T_j=150^{\circ}\text{C}$ ,  $V_{CE}=600\text{V}$ ,  $V_{GE}=0/15\text{V}$ ,  $I_C=40\text{A}$ , Dynamic test circuit in Figure D)

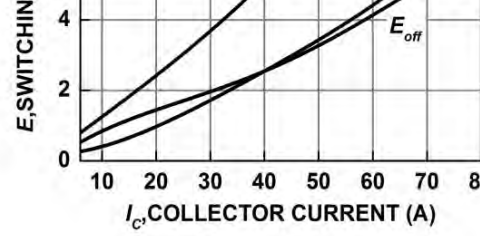


Figure 10. Typical switching energy losses as a function of collector current (inductive load,  $T_j=150^{\circ}\text{C}$ ,  $V_{GE}=0/15\text{V}$ ,  $R_G=12\Omega$ , Dynamic test circuit in Figure D)



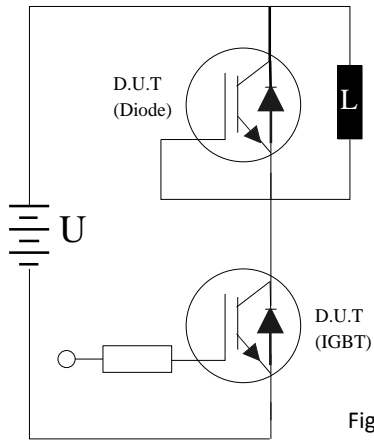


Figure D. Dynamic test circuit



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